

# CD74FCT273

**BiCMOS FCT Interface Logic,** 

**Octal D Flip-Flop with Reset** 

Data sheet acquired from Harris Semiconductor

• Typical Propagation Delay: 5.3ns at V<sub>CC</sub> = 5V,

• SCR Latchup Resistant BiCMOS Process and

January 1997

**Features** 

· Buffered Inputs

 $T_A = 25^{\circ}C, C_L = 50pF$ 

# NOT RECOMMENDED FOR NEW DESIGNS Use CMOS Technology

### **Circuit Design**

- Speed of Bipolar FAST™/AS/S
- 48mA Output Sink Current
- Output Voltage Swing Limited to 3.7V at V<sub>CC</sub> = 5V
- Controlled Output Edge Rates
- Input/Output Isolation to V<sub>CC</sub>
- BiCMOS Technology with Low Quiescent Power

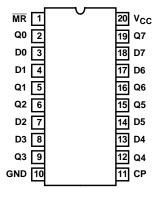
#### Ordering Information

PART NUMBER	TEMP. RANGE ( <sup>O</sup> C)	PACKAGE	PKG. NO.
CD74FCT273E	0 to 70	20 Ld PDIP	E20.3
CD74FCT273M	0 to 70	20 Ld SOIC	M20.3

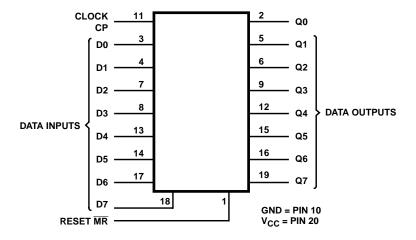
NOTE: When ordering the suffix M package, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.

#### **Pinout**

CD74FCT273 (PDIP, SOIC) **TOP VIEW** 



# Functional Diagram



#### TRUTH TABLE (Note 1)

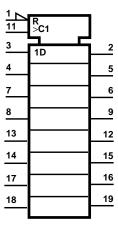
	INPUTS		
RESET MR	CLOCK CP	DATA Dn	Qn
L	X	X	L
Н	1	Н	Н
Н	1	L	L
Н	L	Х	Q0

#### NOTE:

- 1. H = HIGH Voltage Level (Steady State)
  - L = LOW Voltage Level (Steady State)
  - X = Irrelevant
  - $\uparrow$  = Transition from low to high level.
  - Q0 = The level of Q before the indicated steady state input conditions were established.

## IEC Logic Symbol

#### **CD74FCT273**



#### **CD74FCT273**

#### **Absolute Maximum Ratings**

_	
DC Supply Voltage (V <sub>CC</sub> )0.	5V to 6V
DC Input Diode Current, I <sub>IK</sub> (For V <sub>I</sub> < -0.5V)	20mA
DC Output Diode Current, I <sub>OK</sub> (for V <sub>O</sub> < -0.5V)	50mA
DC Output Sink Current per Output Pin, IO	
DC Output Source Current per Output Pin, IO	30mA
DC V <sub>CC</sub> Current (I <sub>CC</sub> )	.140mA
DC Ground Current (ICND)	.400mA

#### **Thermal Information**

Thermal Resistance (Typical, Note 2)	θ <sub>JA</sub> (ºC/W)
PDIP Package	135
SOIC Package	125
Maximum Junction Temperature	150 <sup>o</sup> C
Maximum Storage Temperature Range	65°C to 150°C
Maximum Lead Temperature (Soldering 10s)	
(SOIC-Lead Tips Only)	

#### **Operating Conditions**

Operating Temperature Range (T <sub>A</sub> )	
Supply Voltage Range, VCC	4.75V to 5.25V
DC Input Voltage, V <sub>1</sub>	0 to $V_{\mbox{\footnotesize{CC}}}$
DC Output Voltage, VO	$\dots$ 0 to $\leq$ V <sub>CC</sub>
Input Rise and Fall Slew Rate, dt/dv	0 to 10ns/V

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

#### NOTE

2.  $\theta_{JA}$  is measured with the component mounted on an evaluation PC board in free air.

**Electrical Specifications** Commercial Temperature Range  $0^{\circ}$ C to  $70^{\circ}$ C,  $V_{CC}$  Max = 5.25V,  $V_{CC}$  Min = 4.75V (Note 5)

					AMBIE	NT TEM	PERATUR	RE (T <sub>A</sub> )	
		TEST CO	NDITIONS		25	°C	0°C T	O 70°C	
PARAMETER	SYMBOL	V <sub>I</sub> (V)	I <sub>O</sub> (mA)	V <sub>CC</sub> (V)	MIN	MAX	MIN	MAX	UNITS
High Level Input Voltage	V <sub>IH</sub>			4.75 to 5.25	2	-	2	-	V
Low Level Input Voltage	V <sub>IL</sub>			4.75 to 5.25	-	0.8	-	0.8	V
High Level Output Voltage	Voн	V <sub>IH</sub> or V <sub>IL</sub>	-15	Min	2.4	-	2.4	-	V
Low Level Output Voltage	V <sub>OL</sub>	V <sub>IH</sub> or V <sub>IL</sub>	48	Min	-	0.55	-	0.55	V
High Level Input Current	I <sub>IH</sub>	V <sub>CC</sub>		Max	-	0.1	-	1	μΑ
Low Level Input Current	I <sub>IL</sub>	GND		Max	-	-0.1	-	-1	μΑ
Three State Leakage Current	l <sub>OZH</sub>	V <sub>CC</sub>		Max	-	0.5	-	10	μΑ
	lozL	GND		Max	-	-0.5	-	-10	μΑ
Input Clamp Voltage	V <sub>IK</sub>	V <sub>CC</sub> or GND	-18	Min	-	-1.2	-	-1.2	V
Short Circuit Output Current (Note 3)	los	V <sub>O</sub> =0 V <sub>CC</sub> or GND		Max	-60	-	-60	-	mA
Quiescent Supply Current, MSI	Icc	V <sub>CC</sub> or GND	0	Max	-	8	-	80	μΑ
Additional Quiescent Supply Current per Input Pin TTL Inputs High, 1 Unit Load	Δl <sub>CC</sub>	3.4V (Note 4)		Max	-	1.6	-	1.6	mA

#### NOTES:

- 3. Not more than one output should be shorted at one time. Test duration should not exceed 100ms.
- 4. Inputs that are not measured are at  $V_{CC}$  or GND.
- 5. FCT Input Loading: All inputs are 1 unit load. Unit load is  $\Delta I_{CC}$  limit specified in Static Characteristics Chart, e.g., 1.6mA Max. at  $70^{\circ}C$ .

#### **CD74FCT273**

#### Switching Specifications Over Operating Range FCT Series $t_r$ , $t_f$ = 2.5ns, $C_L$ = 50pF, $R_L$ (Figure 4) (Note 6)

				0°C TO 70°C		
PARAMETER	SYMBOL	V <sub>CC</sub> (V)	TYP	MIN	MAX	UNITS
Propagation Delays						
CP to Qn	t <sub>PLH</sub> , t <sub>PHL</sub>	5	7	2	13	ns
MR to Qn	t <sub>PLH</sub> , t <sub>PHL</sub>	5	8	2	13	ns
Power Dissipation Capacitance	C <sub>PD</sub> (Note 7)	-	36	-	i	pF
Input Capacitance	C <sub>I</sub>	-	-	-	10	pF

#### NOTES:

6. 5V: Min is at 5.25V for  $0^{\circ}$ C to  $70^{\circ}$ C, Max is at 4.75V for  $0^{\circ}$ C to  $70^{\circ}$ C, Typ is at 5V.

7. C<sub>PD</sub>, measured per flip-flop, is used to determine the dynamic power consumption.

PD, measured per nip-nop, is used to determine the dynamic power consumption. PD (per package) =  $V_{CC} I_{CC} + \Sigma (V_{CC}^2 I_{I} C_{PD} + V_{O}^2 I_{O} C_{L} + V_{CC} \Delta I_{CC} D)$  where:  $V_{CC}$  = supply voltage  $\Delta I_{CC}$  = flow through current x unit load  $C_{L}$  = output load capacitance D = duty cycle of input high

f<sub>O</sub> = output frequency

f<sub>I</sub> = input frequency

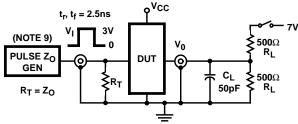
#### Prerequisite for Switching (Note 8)

			25°C	0°C TO 70°C		
PARAMETER	SYMBOL	V <sub>CC</sub> (V)	TYP	MIN	MAX	UNITS
Data to CP Setup Time	tsu	5	-	3	-	ns
Hold Time	t <sub>H</sub>	5	-	2	-	ns
Removal Time, MR to CP	t <sub>REM</sub>	5	-	4	-	ns
MR Pulse Width	t <sub>W</sub>	5	-	7	-	ns
CP Pulse Width	t <sub>W</sub>	5	-	7	-	ns
CP Frequency	f <sub>MAX</sub>	5	-	70	-	MHz

#### NOTE:

8. 5V: Minimum is at 4.75V for 0°C to 70°C, Typical is at 5V.

#### Test Circuits and Waveforms



#### NOTE:

9. Pulse Generator for All Pulses: Rate  $\leq$  1.0MHz;  $Z_{\mbox{OUT}} \leq$  500;  $t_{\mbox{f}},\,t_{\mbox{f}} \leq$  2.5ns.

FIGURE 1. TEST CIRCUIT

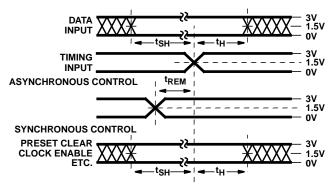


FIGURE 2. SETUP, HOLD, AND RELEASE TIMING

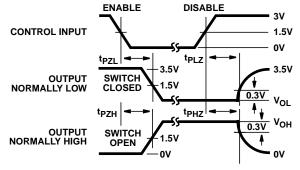


FIGURE 4. ENABLE AND DISABLE TIMING

#### **SWITCH POSITION**

TEST	SWITCH
t <sub>PLZ</sub> , t <sub>PZL</sub> , Open Drain	Closed
t <sub>PHZ</sub> , t <sub>PZH</sub> , t <sub>PLH</sub> , t <sub>PHL</sub>	Open

#### DEFINITIONS:

C<sub>L</sub> = Load capacitance, includes jig and probe capacitance.

 $R_T$  = Termination resistance, should be equal to  $Z_{OUT}$  of the Pulse Generator.

 $V_{IN} = 0V$  to 3V.

Input:  $t_r = t_f = 2.5$ ns (10% to 90%), unless otherwise specified

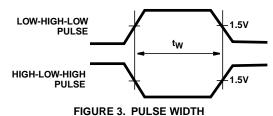


FIGURE 3. PULSE WIDTH

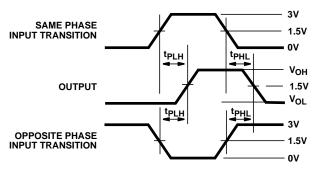
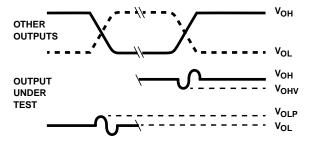


FIGURE 5. PROPAGATION DELAY





#### NOTES:

- 10.  $V_{OLP}$  is measured with respect to a ground reference near the output under test.  $V_{OHV}$  is measured with respect to  $V_{OH}$ .
- 11. Input pulses have the following characteristics:  $P_{RR} \le 1 MHz$ ,  $t_f = 2.5 ns$ ,  $t_f = 2.5 ns$ , skew 1ns.
- 12. R.F. fixture with 700MHz design rules required. IC should be soldered into test board and bypassed with 0.1μF capacitor. Scope and probes require 700MHz bandwidth.

#### FIGURE 6. SIMULTANEOUS SWITCHING TRANSIENT WAVEFORMS

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